

N-Channel Enhancement Mode Dual DMOS FET



SD411

FEATURES

- Normally "OFF" Configuration
- High Speed Switching under 1 ns (typically)
- Ultra Low Capacitance $C_{iss} < 3.5$ pf (typically)
- Tight Matching Characteristics
- Pin Compatible to Industry Standard
Dual JFETs with Addition of Substrate Bias Pin

APPLICATIONS

- Wideband Differential Amplifiers
- Cascode Amplifiers
- High Intercept Point Balanced Mixers
- Oscillators
- High Speed Analog Comparators

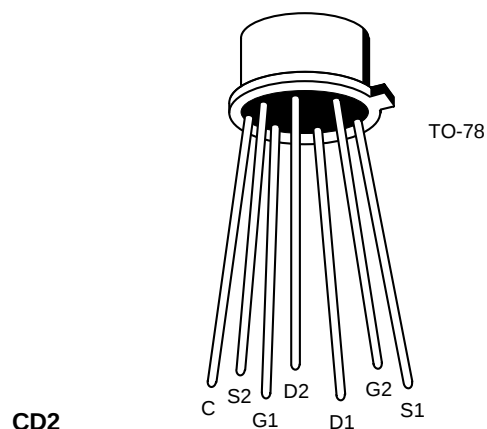
DESCRIPTION

The SD411 is constructed utilizing Calogic's high speed lateral DMOS techniques featuring tight matching characteristics between each FET. This device is an excellent choice for instrumentation, communication, RF and Video designs.

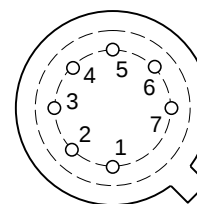
ORDERING INFORMATION

Part	Package	Temperature Range
SD411	TO-78 Hermetic Package	-55°C to +150°C
XSD411	Sorted Chips in Carriers	-55°C to +150°C

PIN CONFIGURATION



- 1 SOURCE 1
- 2 DRAIN 1
- 3 GATE 1
- 4 CASE/BODY
- 5 SOURCE 2
- 6 DRAIN 2
- 7 GATE 2



BOTTOM VIEW

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

V_{DS}	Drain-Source Voltage	+20V	P_D	Device Dissipation (each side)	360 mW
V_{SD}	Source-Drain Voltage	+10V		Derating Factor	2.88 mW/ $^{\circ}\text{C}$
V_{DB}	Drain-Body voltage	+25V	P_D	Total Device Dissipation	500 mW
V_{SB}	Source-Body Voltage	+15V		Derating Factor	4 mW/ $^{\circ}\text{C}$
V_{GD}	Gate-Drain Voltage	+25V	T_j	Operating Junction	
V_{GS}	Gate-Source Voltage	+25V		Temperature Range	-55 to +125 $^{\circ}\text{C}$
V_{GB}	Gate-Body Voltage	+25V	T_S	Storage Temperature Range	-55 to +150 $^{\circ}\text{C}$
V_{G1G2}	Gate-to-Gate Voltage	+25V	T_L	Lead Temperature (1/16" from mounting surface for 10 sec.)	+260 $^{\circ}\text{C}$
V_{D1D2}	Drain-to-Drain Voltage	+20V			
V_{S1S2}	Source-to-Source Voltage	+15V			
I_D	Continuous Drain Current	+50 mA			

ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}\text{C}$ per side unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
STATIC							
BV _{DS}	Drain Source Breakdown Voltage	20			V	I _D = 10 nA, V _{GS} = V _{BS} = -5V	
BV _{SD}	Source-Drain Breakdown Voltage	10				I _S = 10 nA, V _{GD} = V _{BD} = -5V	
BV _{DB}	Drain-Body Breakdown Voltage	25				I _D = 10 nA, V _{GB} = 0 Source Open	
BV _{SB}	Source-Body Breakdown Voltage	15				I _S = 10μA, V _{GB} = 0 Drain Open	
I _{DSX}	Drain-Source Leakage Current		0.7	10	nA	V _{DS} = 20V, V _{GS} = V _{BS} = -5V	
I _{GBS}	Gate-Body Leakage Current			1.0	μA	V _{GS} = 25V, V _{DB} = V _{SB} = 0	
V _{GS(th)}	Gate-Source Threshold Voltage	0.5	1.0	2.0	V	I _D = 1.0μA, V _{DS} = V _{GS} , V _{SB} = 0	
r _{DS(ON)}	Drain-Source ON Resistance ⁽¹⁾			70	ohms	I _D = 1.0mA, V _{GS} = 5.0V, V _{SB} = 0	
DYNAMIC							
g _{fs}	Common-Source Forward Transconductance ⁽¹⁾	10	12		mS	V _{DS} = 10V, I _D = 20mA, V _{SB} = 0 f = 1KHZ	
C _{iss}	Common-Source Input Capacitance		3.5		pF	V _{DS} = 10V, V _{GS} = V _{BS} = 0 f = 1MHZ	
C _{oss}	Common-Source Output Capacitance		1.2				
C _{rss}	Common Source Reverse Transfer Capacitance		0.3				
C _(gs + sb)	Source Node Capacitance		4.5				
MATCH							
V _{GS1} - V _{GS2}	Differential Gate Source Voltage		25		mV	V _{DS} = 10V I _D = 5.0mA V _{SB} = 0	
$\frac{\Delta V_{GS1} - V_{DS2} }{\Delta T}$	Differential Drift		25		μV/ °C		T _A = -55°C to +125C°

NOTE 1: Pulse Test, 80sec, 1% Duty Cycle